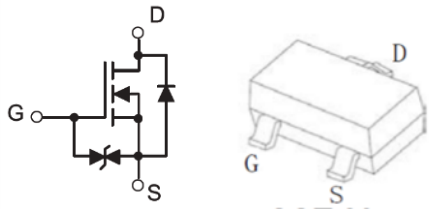
2SK3018

30V/0.1A N-Channel Advanced Power MOSFET

Features

- Low on-resistance
- Fast switching speed
- Low voltage drive (2.5V) makes this device ideal for portable equipment
- Easily designed drive circuits.
- Easy to parallel.

BVDSS	30	V
ID	0.1	A
RDSON@VGS=4V	5	Ω
RDSON@VGS=2.5V	7	Ω



SOT-23

Applications

- Interfacing, switching

Order Information

Product	Package	Marking	Reel Size	Reel	Carton
2SK3018	SOT-23	KN	7inch	3000PCS	180000PCS

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	TA =25°C	0.1	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested (Sillicon Limit) (Note1)	TA =25°C	0.4	A
I_D	Continuous Drain current	TA =25°C	0.1	A
P_D	Maximum Power Dissipation	TA =25°C	0.2	W
$R_{\theta JA}$	Thermal Resistance Junction−to−Ambient (Note2)		625	°C/W

30V/0.1A N-Channel Advanced Power MOSFET

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain- Source Breakdown Voltage	VGS=0V ID=250μA	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain current	VDS=30V,VGS=0V	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±1	μA
$V_{GS(TH)}$	Gate Threshold Voltage	VDS=VGS,ID=100μA	0.8	--	1.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance (Note3)	VGS=4V, ID=0.01A	--	5	8	Ω
		VGS=2.5V, ID=0.001A	--	7	13	Ω
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) (Note4)						
C_{iss}	Input Capacitance	VDS=5V, VGS=0V, F=1MHz	--	13	--	pF
C_{oss}	Output Capacitance		--	9	--	pF
C_{rss}	Reverse Transfer Capacitance		--	4	--	pF
Switching Characteristics (Note4)						
$t_{d(on)}$	Turn-on Delay Time	VDS=5V, ID=0.01A, RL=500Ω, RG=10Ω, VGS=5V	--	15	--	nS
t_r	Turn-on Rise Time		--	35	--	nS
$t_{d(off)}$	Turn-off Delay Time		--	80	--	nS
t_f	Turn-off Fall Time		--	80	--	nS

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
4. Guranteed by design, not subject to production testing.

30V/0.1A N-Channel Advanced Power MOSFET

Typical Characteristics

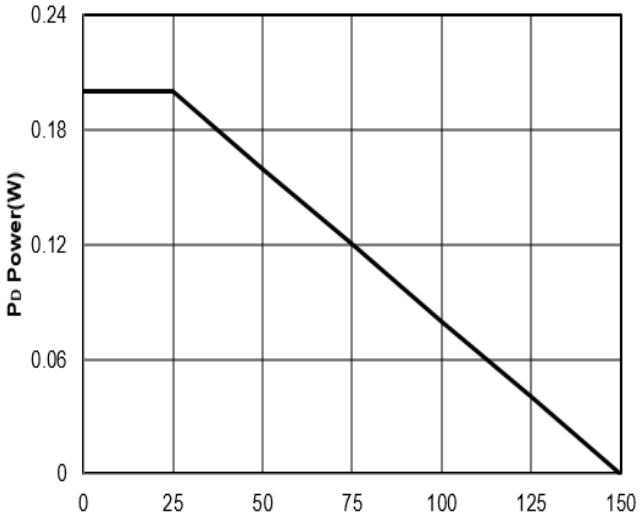


Figure1：T_J Junction Temperature（°C）

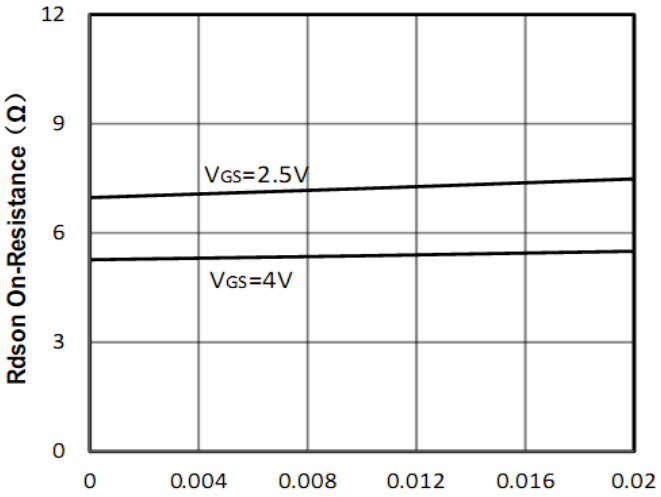


Figure2：I_D Drain Current（A）

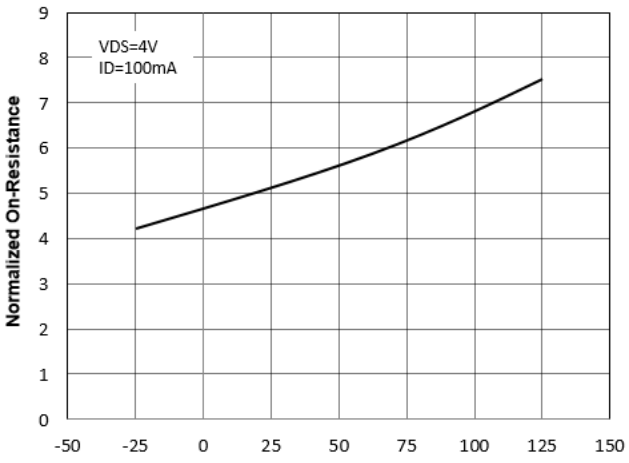


Figure3：T_J Junction Temperature（°C）

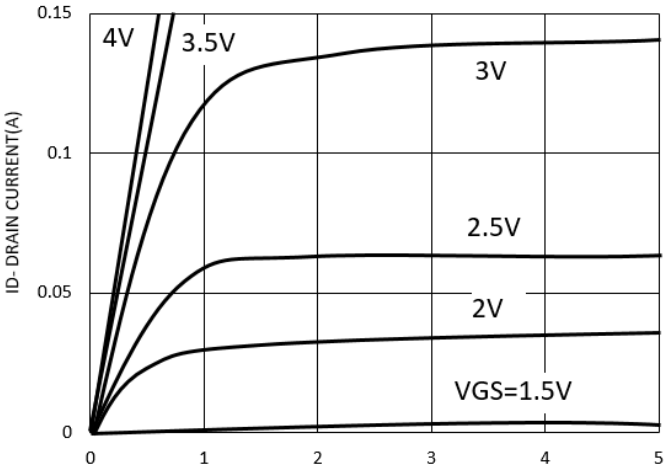


Figure4：V_{DS} Drain-Source Voltage（A）

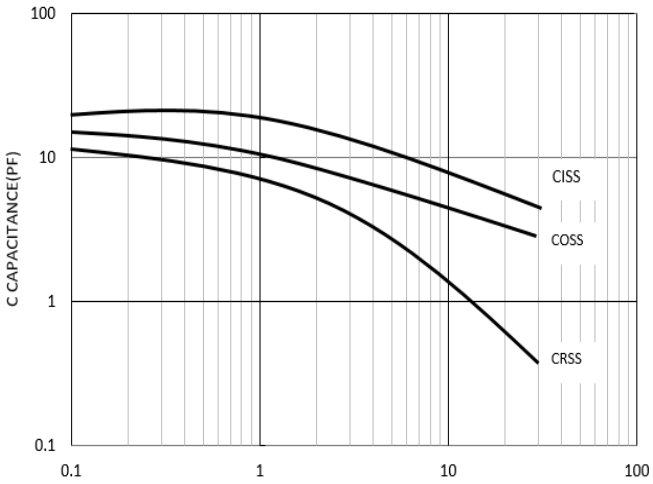


Figure5：V_{DS} Drain-Source Voltage（V）

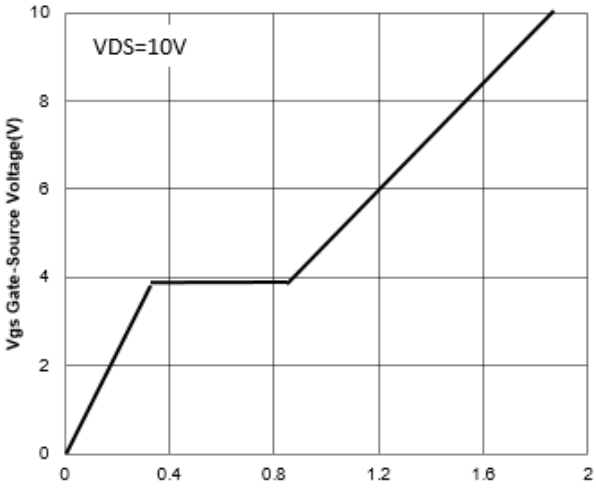


Figure6：Qg Gate Charge（nC）

30V/0.1A N-Channel Advanced Power MOSFET

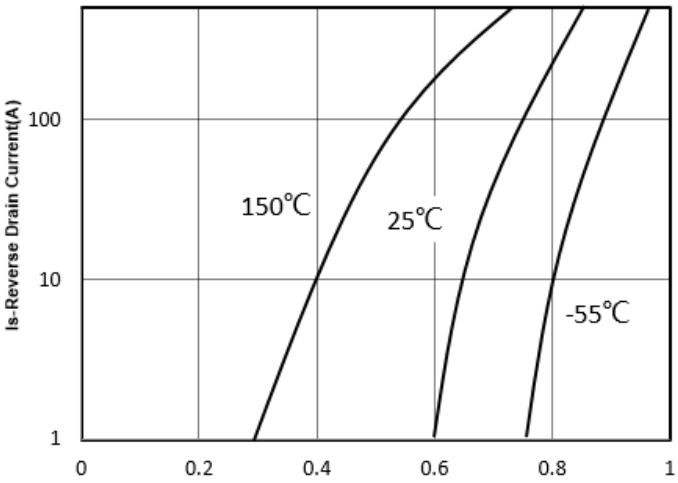


Figure7：Vsd Source-Drain Voltage（V）

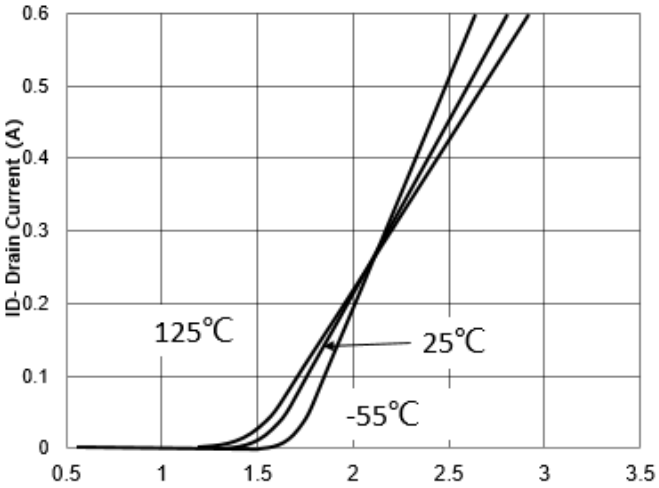


Figure8：Vgs Gate-Source Voltage（V）

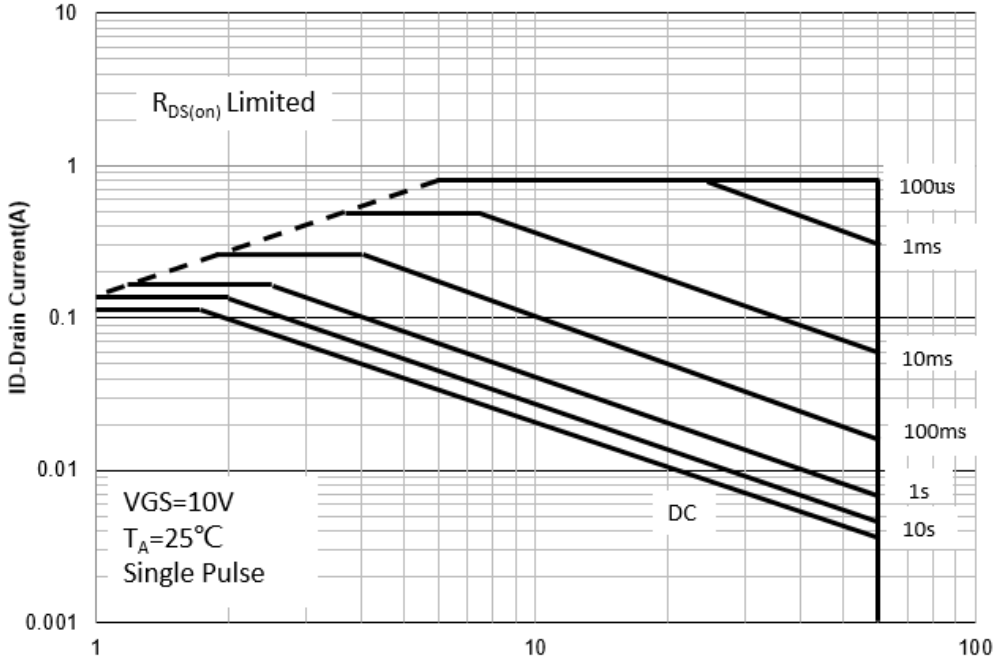


Figure9：Vsd Drain -Source Voltage（V）

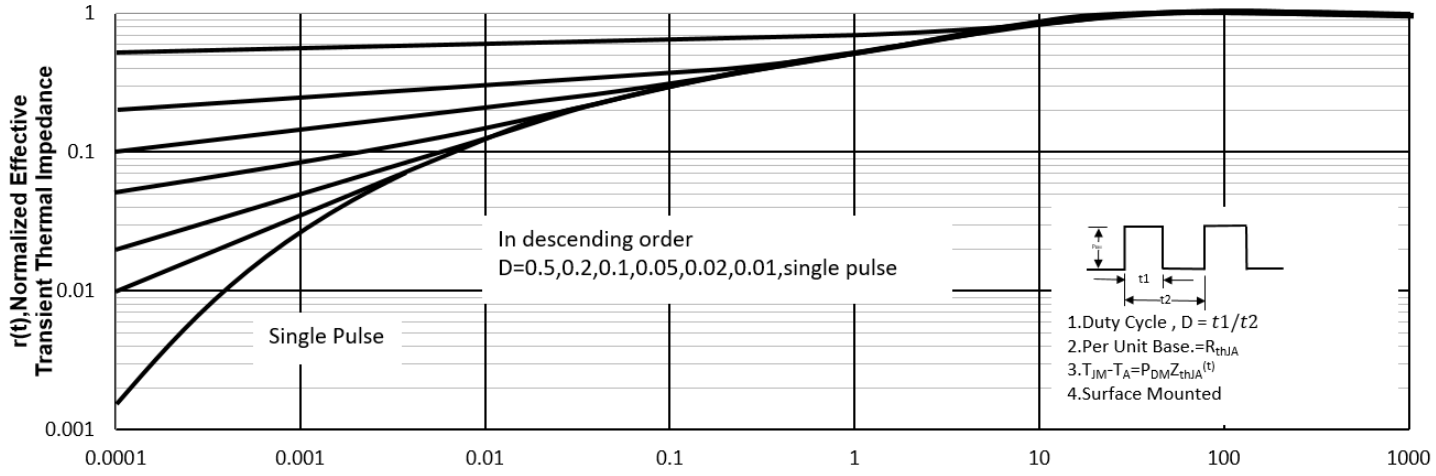


Figure10：Square Wave Pulse Duration（sec）

30V/0.1A N-Channel Advanced Power MOSFET

Test Circuit and Waveform:

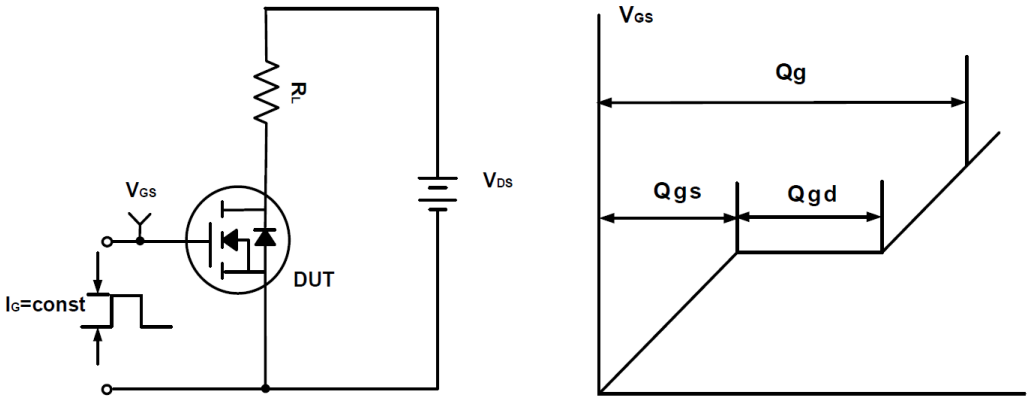


Figure A Gate Charge Test Circuit &Waveforms

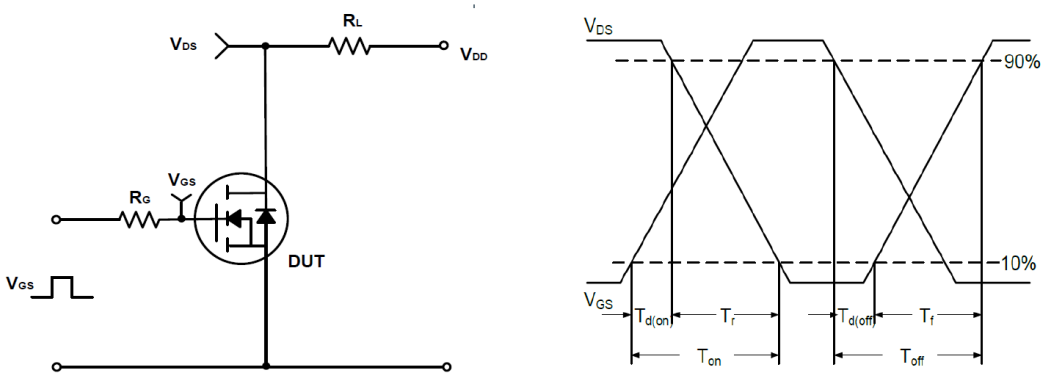


Figure B Switching Test Circuit & Waveforms

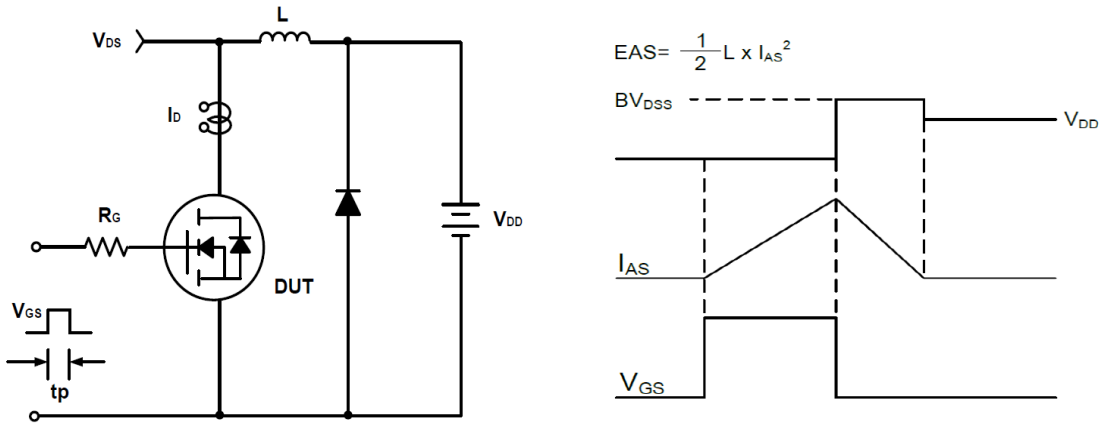
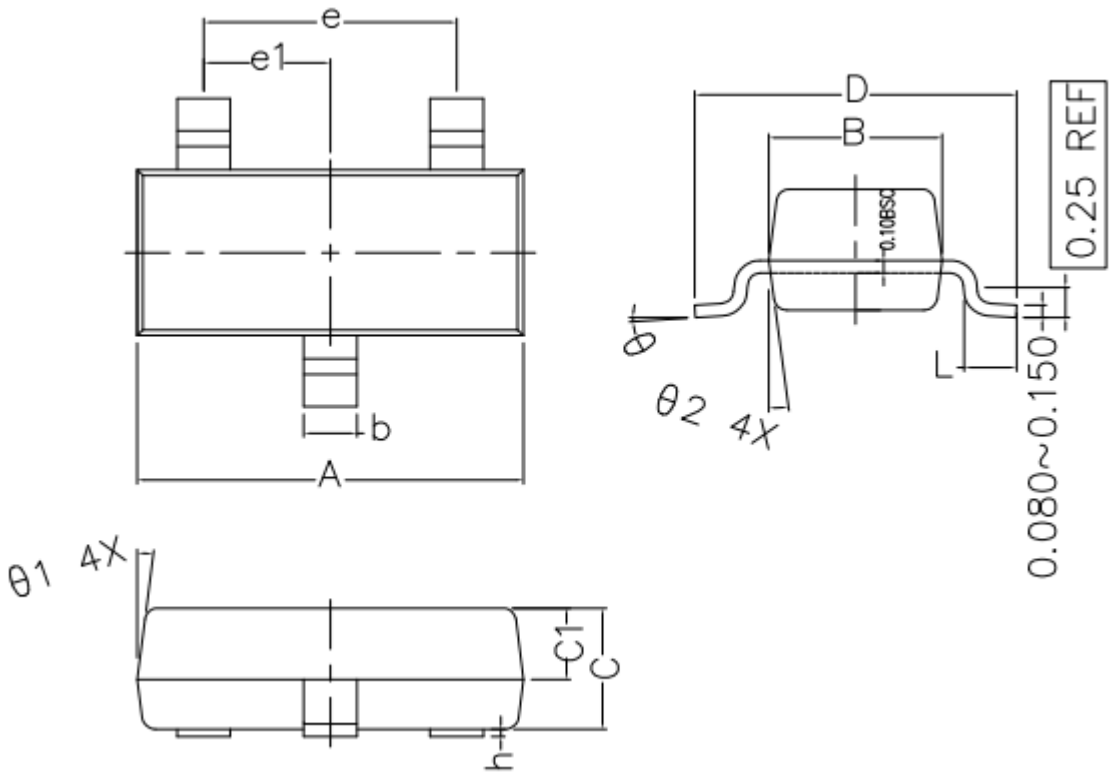


Figure C Unclamped Inductive Switching Circuit & Waveforms

30V/0.1A N-Channel Advanced Power MOSFET

SOT-23 Package Outline Dimensions (Units: mm)



COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	2.800	2.900	3.000
B	1.200	1.300	1.400
C	0.900	1.000	1.100
C1	0.500	0.550	0.600
D	2.250	2.400	2.550
L	0.300	0.400	0.500
h	0.010	0.050	0.100
b	0.300	0.400	0.500
e	1.90 TYPE		
e1	0.95 TYPE		
θ_1	7° TYPE		
θ_2	7° TYPE		
θ	0° ~ 7°		